

1N5774

Isolated Diode Array with HiRel MQ, MX, MV, and MSP Screening Options

DESCRIPTION

These low capacitance diode arrays are multiple, discrete, isolated junctions fabricated by a planar process and mounted in a 14-PIN package for use as steering diodes protecting up to eight I/O ports from ESD, EFT, or surge by directing them to the positive side of the power supply line and to ground (see figure 1). An external TVS diode may be added between the positive supply line and ground to prevent overvoltage on the supply rail. They may also be used in fast switching core-driver applications. This includes computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, etc., as well as decoding or encoding applications. These arrays offer many advantages of integrated circuits such as high-density packaging and improved reliability. This is a result of fewer pick and place operations, smaller footprint, smaller weight, and elimination of various discrete packages that may not be as user friendly in PC board mounting.



Flat Pack

IMPORTANT: For the most current data, consult *MICROSEMI's* website: <u>http://www.microsemi.com</u>

FEATURES	APPLICATIONS / BENEFITS
 Hermetic Ceramic Package Isolated Diodes To Eliminate Cross-Talk Voltages High Breakdown Voltage V_{BR} > 60 V at 10 μA Low Leakage I_R< 100nA at 40 V Low Capacitance C < 8.0 pF Options for screening in accordance with MIL-PRF- 19500/474 for JAN, JANTX, JANTXV, and JANS are available by adding MQ, MX, MV, or MSP prefixes respectively to part numbers. For example, designate MX1N5774 for a JANTX screen. 	 High Frequency Data Lines RS-232 & RS-422 Interface Networks Ethernet: 10 Base T Computer I/O Ports LAN Switching Core Drivers IEC 61000-4 Compatible (see circuit in figure 1) 61000-4-2 ESD: Air 15 kV, contact 8 kW 61000-4-4 (EFT): 40 A – 5/50 ns 61000-4-5 (surge): 12 A 8/20 μs
MAXIMUM RATINGS	MECHANICAL AND PACKAGING
 Reverse Breakdown Voltage of 60 Vdc (Note 1 & 2) Continuous Forward Current of 300 mA dc (Note 1 & 3) Peak Surge Current (tp=1/120 s) of 500 mA dc (Note 1) 400 mW Power Dissipation per Junction @ 25°C 500 mW Power Dissipation per Package @ 25°C (Note 4) Operating Junction Temperature range –65 to +150°C Storage Temperature range of –65 to +200°C NOTE 1: Each Diode 	 14-PIN Ceramic Flat Pack Weight 0.29 grams (approximate) Marking: Logo, part number, date code and dot identifying pin #1 Carrier Tubes; 19 pcs (standard)

- **NOTE 2:** Pulsed: $P_W = 100 \text{ ms max.}$; duty cycle $\leq 20\%$ **NOTE 3:** Derate at 2.4 mA/°C above $+25^{\circ}C$
 - **NOTE 4:** Derate at 4.0 mW/°C above +25°C

ELECTRICAL CHARACTERISTICS (Per Diode) @ 25°C unless otherwise specified

	MAXIMUM FORWARD VOLTAGE V _{F1} I _F = 100 mA	MAXIMUM FORWARD VOLTAGE V _{F2} I _F = 500 mA	MAXIMUM REVERSE CURRENT I _{R1}	MAXIMUM CAPACITANCE (PIN TO PIN) C _t V _R = 0 V	MAXIMUM FORWARD RECOVERY TIME t _{fr}	MAXIMUM REVERSE RECOVERY TIME trr I _F = I _R = 200 mA i _{rr} = 20 mA	
PART	(Note 1)	(Note 1)	$V_{R} = 40 V$	F = 1 MHz	I _F = 500 mA	R _L = 100 ohms	
NUMBER	Vdc	Vdc	μAdc	pF	ns	ns	
1N5774	1	1.5	0.1	8.0	40	20	

NOTE 1: Pulsed: $P_W = 300 \ \mu s \ +/- 50 \ \mu s$, duty cycle $\leq 2\%$, 90 μs after leading edge.

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		DEFIN					
V_{BR}	Minimum Breakdown Volta						
V _F	Maximum Forward Voltage	e: The maximum for	ward voltage t	he devic	e will exl	hibit at a	specifi
I _R	Maximum Leakage Current: The maximum leakage current that will flow at the speci						ied volta
	temperature. Capacitance: The capacita	ance of the TVS as o	lefined @ 0.vc	olts at a f	requenc	v of 1 M	Hz and
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				BW2	⊨— В₩ — =Г ⇒ В₩1 •	■ = 	LL —
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	CIRCUIT		<u>+</u> +	.L — — — — — — — — — — — — — — — — — — —	⊨— В₩ — = = = В₩1 •	= = 	2
				-			-
	CIRCUIT		<u>+</u> +	Inc	hes	Milli	meters
	CIRCUIT		Symbol	-	hes Max		meters Max
	CIRCUIT		Symbol BL	Inc Min	hes Max .390	Milli Min	meters Max 9.91
	CIRCUIT		Symbol BL BW	Inc Min .235	hes Max .390 .260	Milli Min 5.97	meters Max 9.91 6.60
Supply	CIRCUIT		Symbol BL	Inc Min .235 .045	hes <u>Max</u> .390 .260 .095	Millin Min 5.97 1.14	meters Max 9.91
Supply	CIRCUIT		Symbol BL BW CH	Inc Min .235	hes Max .390 .260	Milli Min 5.97	meters Max 9.91 6.60 2.41
Supply	CIRCUIT		Symbol BL BW CH LL	Inc Min .235 .045 .250	hes <u>Max</u> .390 .260 .095	Millin Min 5.97 1.14 6.35	meters Max 9.91 6.60 2.41
Supply O Port —	CIRCUIT Trail (+V _{CC})		Symbol BL BW CH LL LO	Inc Min .235 .045 .250 .005 .026	hes <u>Max</u> .390 .260 .095 .370	Millin Min 5.97 1.14 6.35 0.13 0.66	meters Max 9.91 6.60 2.41 9.40
Supply O Port —	CIRCUIT		Symbol BL BW CH LL LO LO2	Inc Min .235 .045 .250 .005 .026	hes Max .390 .260 .095 .370 .045	Millin Min 5.97 1.14 6.35 0.13 0.66	meters Max 9.91 6.60 2.41 9.40 1.14
Supply O Port — GNE	CIRCUIT Trail (+V _{CC})		Symbol BL BW CH LL LO LO LO 2 LS	Inc Min .235 .045 .250 .005 .026 .050	hes Max .390 .260 .095 .370 .045 BSC	Millin Min 5.97 1.14 6.35 0.13 0.66 1.27	meters Max 9.91 6.60 2.41 9.40 1.14 7BSC



SYMBOLS & DEFINITIONS



Symbol	Inches		Millimeters		
	Min	Max	Min	Max	
BL		.390		9.91	
BW	.235	.260	5.97	6.60	
СН	.045	.095	1.14	2.41	
LL	.250	.370	6.35	9.40	
LO	.005		0.13		
LO ₂	.026	.045	0.66	1.14	
LS	.050 BSC		1.27 BSC		
LT	.003	.006	0.08	0.15	
LU		.280		7.11	
LW	.010	.019	0.25	0.48	